

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yoshiaki ASAO, et al.

SERIAL NO: NEW APPLICATION

GAU:

FILED: HEREWITH

EXAMINER:

FOR: MAGNETIC RANDOM ACCESS MEMORY HAVING MEMORY CELLS CONFIGURED BY USE OF
TUNNELING MAGNETORESISTIVE ELEMENTS

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

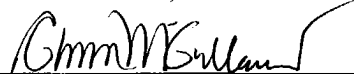
- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Marvin J. Spivak

Registration No. 24,913



22850

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MAIER & NEUSTADT, P.C.



Marvin J. Spivak

Registration No. 24,913

C. Irvin McClelland
Registration Number 21,124



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SERIAL NO.: New Application

FILED: Herewith

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CONFIGURED BY USE OF TUNNELING MAGNETORESISTIVE ELEMENTS

STATEMENT OF RELEVANCY

Reference AW on Form PTO-1449:

This publication is referred to in the specification. (See page 1, line 26.)

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| Form PTO 1449 (Modified) | | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | | ATTY DOCKET NO. 240374US2S | | SERIAL NO. NEW APPLICATION | |
| LIST OF REFERENCES CITED BY APPLICANT | | | | APPLICANT Yoshiaki ASAO, et al. | | | |
| | | | | FILING DATE HEREWITH | | GROUP | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
| | AA | 5,734,605 | 3/31/98 | Xiaodong T. ZHU, et al. | | | |
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| OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.) | | | | | | | |
| | AW | Roy SCHEUERLEIN, et al. "A 10NS READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL," ISSCC 2000 Technical Digest, Session 7, 2000, pgs. 128-129. | | | | | |
| | AX | | | | | | |
| | AY | | | | | | |
| | AZ | | | | | <input type="checkbox"/> Additional References sheet(s) attached | |
| Examiner | | | | | Date Considered | | |
| *Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | |